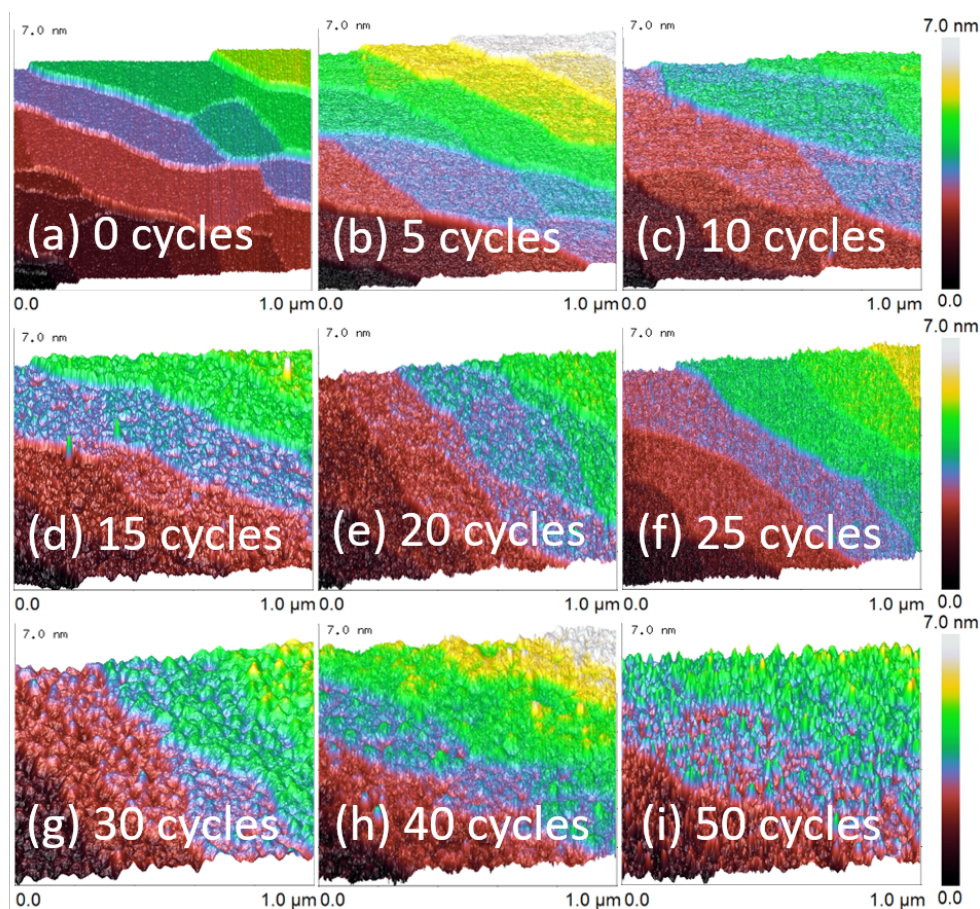


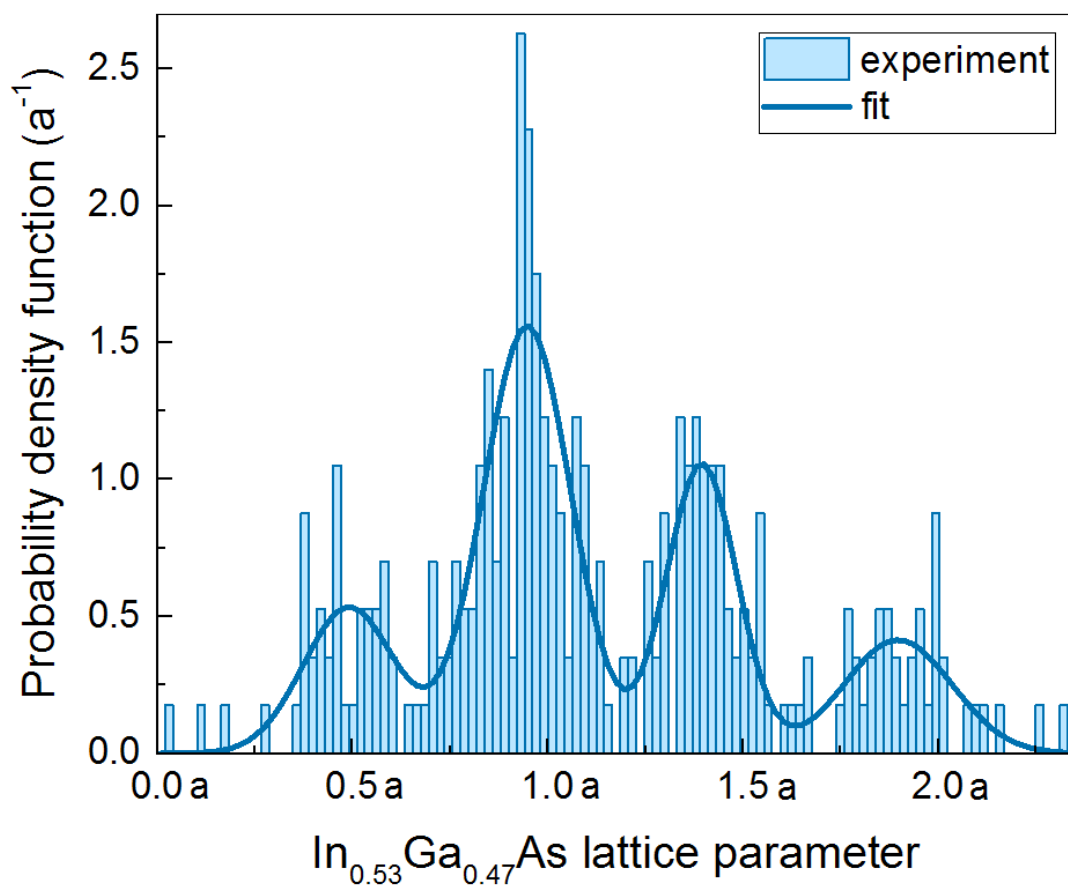
## Supplemental Information

### The Initial Stages of ZnO Atomic Layer Deposition on Atomically Flat $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ Substrates

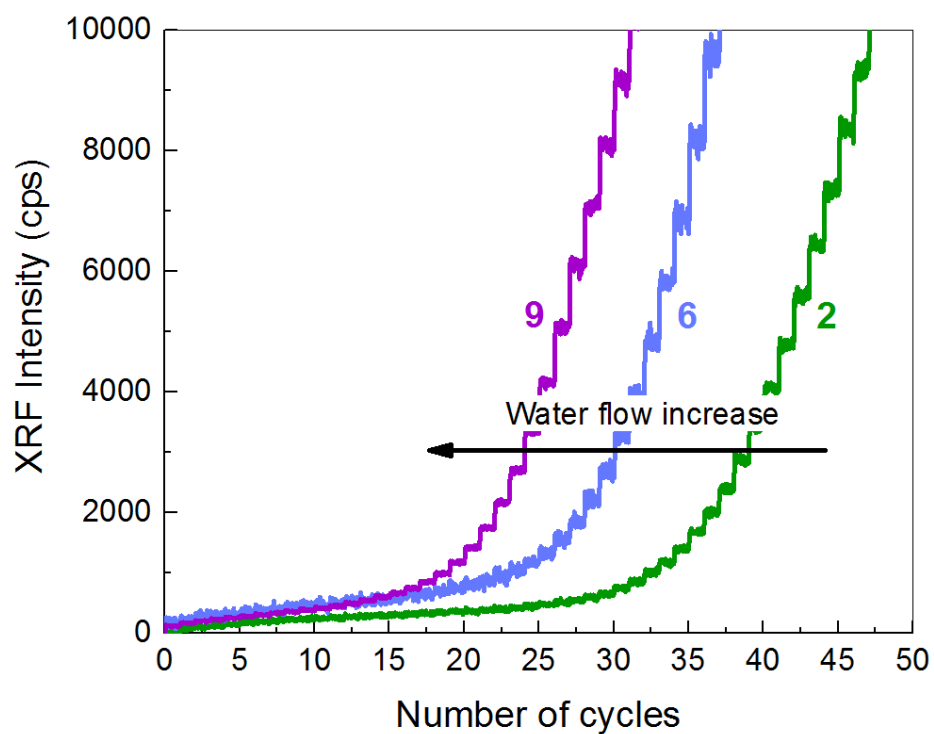
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**Figure S1.** 3D rendering of the same AFM images shown in Fig. 5 of the article, i.e. post-growth AFM images of ZnO films grown on  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$  for different number of cycles: 0 (a), 5 (b), 10 (c), 15 (d), 20 (e), 25 (f), 30 (g), 40 (h) and 50 (i).



**Figure S2.** Statistical distribution of the terrace heights present on the  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$  substrate surface after the 4M HCl etch step. The height value is in  $a$  units, where  $a$  is the bulk  $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$  lattice parameter. A series of parallel lines were chosen with a constant distance between the lines for the analysis. The peaks of the statistical distribution have been approximated by a Gaussian function.



**Figure S3:** Zn K $\alpha$  X-ray fluorescence intensity (T substrate = 120°C) vs. cycle number for three different water flow (deionized water). The increasing of water flow is obtained by opening the injector aperture (2, 6, 9 are the numbers of turns of the manual needle valve). Clearly, increasing the water flow shortens the delay in ZnO nucleation.